IN THE CLAIMS

Please amend the claims as follows.

1. (Previously Presented) A method for providing a uniform oxide layer over a metal layer in a semiconductor device, said method comprising the steps of:

placing a layer of boron doped oxide over said metal layer;

placing a layer of phosphorus doped oxide over said layer of boron doped oxide;

calculating a time period required for a wet etch process to etch through said layer of phosphorus doped oxide; and

performing said wet etch process on said phosphorus doped oxide layer for said time period to etch through the phosphorus doped oxide layer and performing said wet etch process on said boron doped oxide layer after said wet etch process has etched through said phosphorus doped oxide layer to partially etch into the boron doped oxide layer.

2. (Original) The method as set forth in Claim 1 wherein said metal layer in said semiconductor device is a metal link layer of a laser trimmed fuse.

3. (Original) The method as set forth in Claim 1 wherein said step of placing said layer of boron doped oxide over said metal layer comprises the step of:

forming said boron doped oxide layer with a desired thickness.

4. (Original) The method as set forth in Claim 3 wherein said desired thickness of said boron doped oxide layer is approximately five thousand Ångstroms.

5. (Original) The method as set forth in Claim 1 wherein said step of calculating said time period required for said wet etch process to etch through said layer of phosphorus doped oxide comprises the step of:

dividing a thickness of said phosphorus doped oxide layer by a value of an etch rate of said wet etch process through said phosphorus doped oxide layer.

6. (Original) The method as set forth in Claim 1 wherein said step of placing said layer of phosphorus doped oxide over said layer of boron doped oxide comprises the step of:

forming said phosphorus doped oxide layer with a desired thickness.

7. (Original) The method as set forth in Claim 6 wherein said desired thickness of said phosphorus doped oxide layer is approximately five thousand Ångstroms.

8. (Previously Presented) The method as set forth in Claim 1 further comprising the step of:

stopping said wet etch process after said wet etch process has begun to etch said boron doped oxide layer.

9. (Original) The method as set forth in claim 1 further comprising the steps of:

calculating a length of time required for said wet etch process to etch down to a desired thickness of said layer of boron doped oxide; and

performing said wet etch process on said boron doped oxide layer for said length of time after said wet etch process has etched through said phosphorus doped oxide layer.

10. (Original) The method as set forth in Claim 9 wherein said desired thickness of said boron doped oxide layer is approximately five thousand Ångstroms.

Claims 11-20 (Cancelled).

21. (Previously Presented) A method for providing a uniform oxide layer over a metal layer in a semiconductor device, said method comprising the steps of:

placing a layer of a first doped oxide over said metal layer wherein said first doped oxide has a slower etch rate;

placing a layer of a second doped oxide over said layer of said first doped oxide wherein said second doped oxide has a faster etch rate;

calculating a time period required for a wet etch process to etch through said layer of said second doped oxide; and

performing said wet etch process on said layer of said second doped oxide for said time period to etch through the layer of second doped oxide and performing said wet etch process on said layer of first doped oxide after said wet etch process has etched through said layer of second doped oxide to partially etch into the layer of first doped oxide.

22. (Original) The method as set forth in Claim 21 wherein said metal layer in said semiconductor device is a metal link layer of a laser trimmed fuse.

23. (Original) The method as set forth in Claim 21 wherein said step of placing said layer of said first doped oxide over said metal layer comprises the step of:

forming said layer of said first doped oxide with a desired thickness.

24. (Original) The method as set forth in Claim 23 wherein said desired thickness of said layer of said first doped oxide is approximately five thousand Ångstroms.

25. (Original) The method as set forth in Claim 21 wherein said step of calculating said time period required for said wet etch process to etch through said layer of said second doped oxide comprises the step of:

dividing a thickness of said layer of said second doped oxide by a value of an etch rate of said wet etch process through said second doped oxide layer.

26. (Previously Presented) The method as set forth in Claim 21, wherein the first doped oxide comprises boron doped oxide.

27. (Previously Presented) The method as set forth in Claim 21, wherein the second doped oxide comprises phosphorus doped oxide.

28. (Previously Presented) The method as set forth in Claim 27, wherein the wet etch process comprises a fluoride wet etch of the phosphorus doped oxide.

29. (Previously Presented) A method, comprising:

placing a first doped oxide layer over a metal layer in a semiconductor device;

placing a second doped oxide layer over the first doped oxide layer;

calculating a time period required for a wet etch process to etch through the second doped oxide layer; and

performing a wet etch process on the second doped oxide layer for the time period to etch through the second doped oxide layer and performing the wet etch process on the first doped oxide layer after the wet etch process has etched through the second doped oxide layer to partially etch into the first doped oxide layer.

30. (Previously Presented) The method as set forth in Claim 29, wherein placing the first doped oxide layer over the metal layer comprises:

forming the first doped oxide layer with a desired thickness.

31. (Previously Presented) The method as set forth in Claim 30, wherein the desired thickness of the first doped oxide layer is approximately five thousand Ångstroms.

32. (Previously Presented) The method as set forth in Claim 29, wherein calculating the time period required for the wet etch process to etch through the second doped oxide layer comprises:

dividing a thickness of the second doped oxide layer by a value of an etch rate of the wet etch process through the second doped oxide layer.

33. (Previously Presented) The method as set forth in Claim 29, wherein:

the first doped oxide layer comprises a boron doped oxide layer; and

the second doped oxide layer comprises a phosphorus doped oxide layer.

34. (Previously Presented) The method as set forth in Claim 33, wherein the wet etch process comprises a fluoride wet etch of the phosphorus doped oxide layer.

35. (Previously Presented) The method as set forth in Claim 29, further comprising:

laser trimming the metal layer using a laser, wherein the first doped oxide layer has a thickness approximately equal to one-half of a wavelength of the laser.

36. (Previously Presented) The method as set forth in Claim 29 wherein the first doped oxide layer has an etch rate that is at least four hundred times slower than an etch rate of the second doped oxide layer.